STB34N50DM2AG

Automotive-grade N-channel 500 V, 0.10 Ω typ., 26 A MDmesh™ DM2 Power MOSFET in a D²PAK package

Datasheet - production data

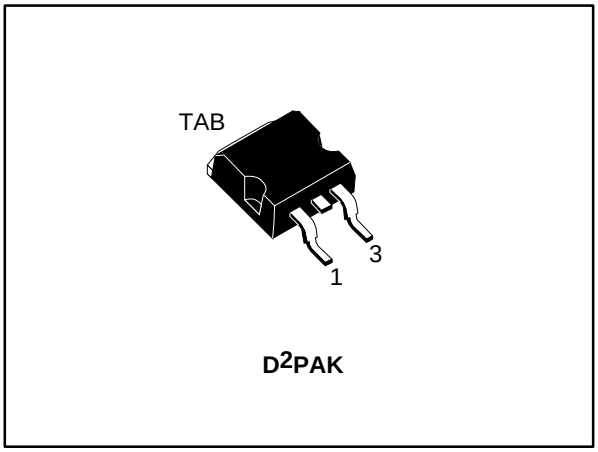
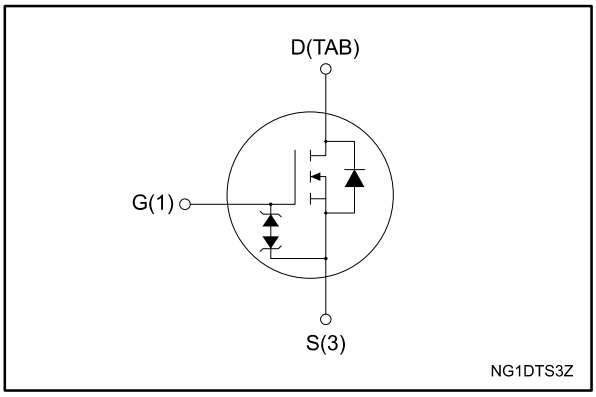


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STB34N50DM2AG	500 V	0.12 Ω	26 A	190 W

- Designed for automotive applications and AEC-Q101 qualified
- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high voltage N-channel Power MOSFET is part of the MDmesh™ DM2 fast recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STB34N50DM2AG	34N50DM2	D²PAK	Tape and reel

This is information on a product in full production.

www.st.com

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_{case} = 25 °C	26	A
	Drain current (continuous) at T_{case} = 100 °C	16	
I_{DM}(1)	Drain current (pulsed)	104	A
P_{TOT}	Total dissipation at T_{case} = 25 °C	190	W
dv/dt(2)	Peak diode recovery voltage slope	50	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Operating junction temperature		

Notes:

(1) Pulse width is limited by safe operating area.

(2) $I_{SD} \leq 26$ A, di/dt=800 A/µs; V_{DS} peak < $V_{(BR)DSS}$,V_{DD} = 80% $V_{(BR)DSS}$.

(3) $V_{DS} \leq 400$ V.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	0.65	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	30	

Notes:

(1) When mounted on a 1-inch² FR-4, 2 Oz copper board.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}(1)	Avalanche current, repetitive or not repetitive	5	A
E_{AS}(2)	Single pulse avalanche energy	700	mJ

Notes:

(1)pulse width limited by T_{jmax}.

(2) starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V.

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	500			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 500 V			10	µA
		V_{GS} = 0 V, V_{DS} = 500 V, T_{case} = 125 °C			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 12.5 A		0.10	0.12	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	1850	-	pF
C_{oss}	Output capacitance		-	100	-	
C_{rss}	Reverse transfer capacitance		-	2.7	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 400 V, V_{GS} = 0 V	-	160	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	4.5	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 25 A, V_{GS} = 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	44	-	nC
Q_{gs}	Gate-source charge		-	10.5	-	
Q_{gd}	Gate-drain charge		-	19	-	

Notes:

(1) $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 250 V, I_D = 12.5 A R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14: "Test circuit for resistive load switching times"* and *Figure 19: "Switching time waveform"*)	-	19.5	-	ns
t_r	Rise time		-	11.5	-	
$t_{d(off)}$	Turn-off delay time		-	65.5	-	
t_f	Fall time		-	8.1	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		26	A
I_{SDM}(1)	Source-drain current (pulsed)		-		104	A
V_{SD}(2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 26 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 25 A, di/dt = 100 A/µs, V_{DD} = 100 V (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	110		ns
Q_{rr}	Reverse recovery charge		-	0.48		µC
I_{RRM}	Reverse recovery current		-	8.8		A
t_{rr}	Reverse recovery time	I_{SD} = 25 A, di/dt = 100 A/µs, V_{DD} = 100 V, T_j = 150 °C (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	190		ns
Q_{rr}	Reverse recovery charge		-	1.52		µC
I_{RRM}	Reverse recovery current		-	16		A

Notes:

(1) Pulse width is limited by safe operating area.

(2) Pulse test: pulse duration = 300 µs, duty cycle 1.5%.

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ±250 µA, I_D = 0 A	±30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

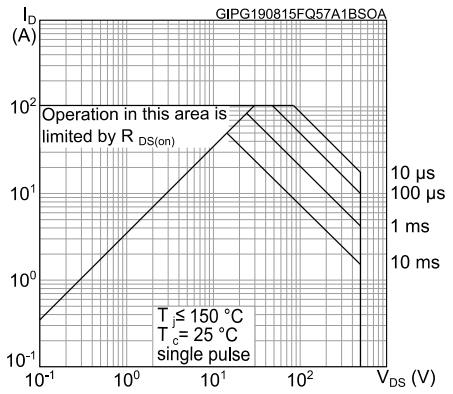


Figure 3: Thermal impedance

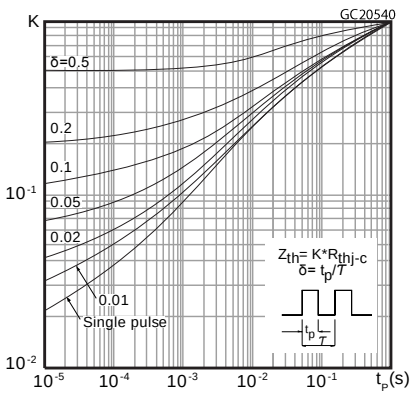


Figure 4: Output characteristics

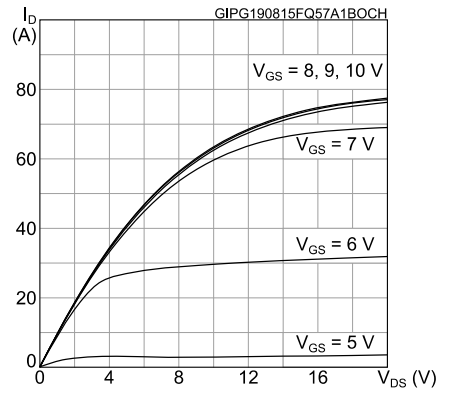


Figure 5: Transfer characteristics

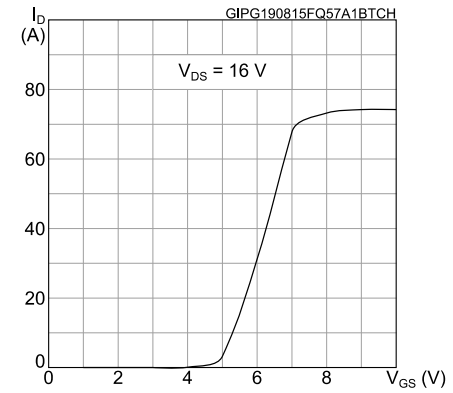


Figure 6: Gate charge vs gate-source voltage

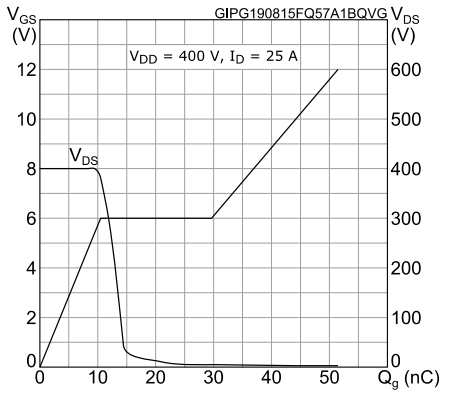


Figure 7: Static drain-source on-resistance

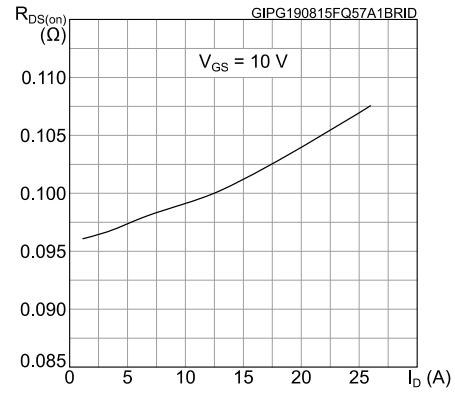


Figure 8: Capacitance variations

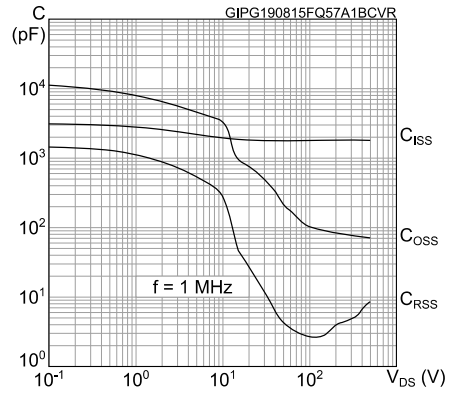


Figure 9: Normalized gate threshold voltage vs temperature

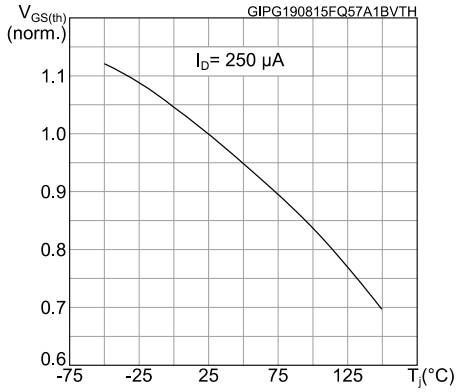


Figure 10: Normalized on-resistance vs temperature

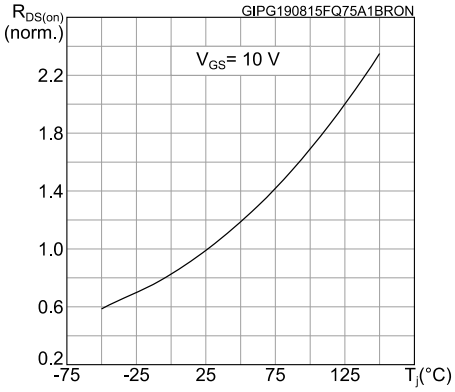


Figure 11: Normalized V(BR)DSS vs temperature

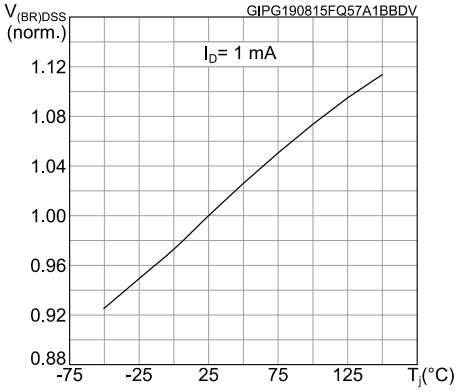


Figure 12: Output capacitance stored energy

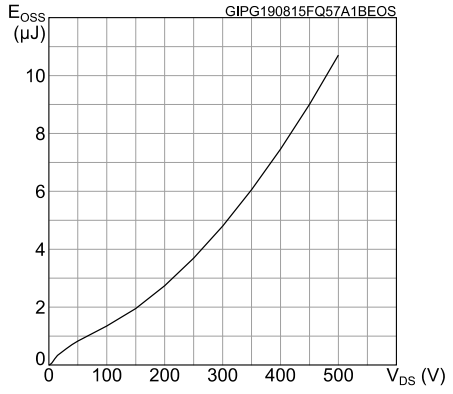
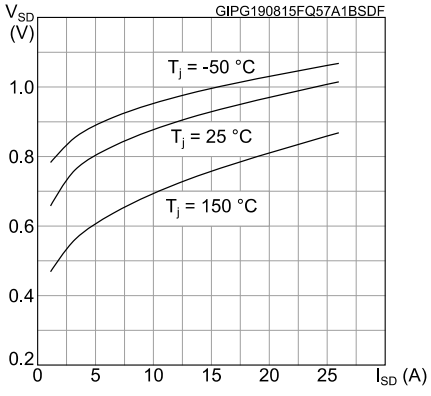


Figure 13: Source- drain diode forward characteristics



3 Test circuits

Figure 14: Test circuit for resistive load switching times

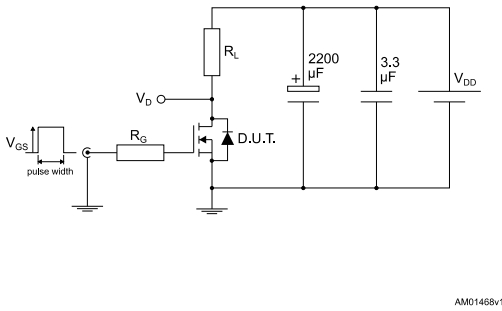


Figure 15: Test circuit for gate charge behavior

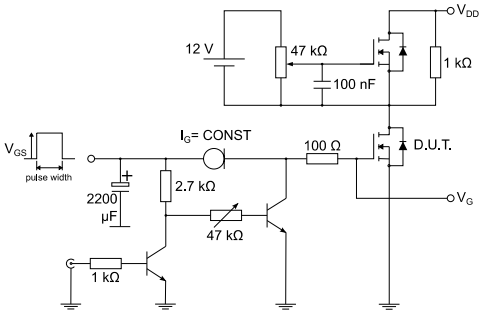


Figure 16: Test circuit for inductive load switching and diode recovery times

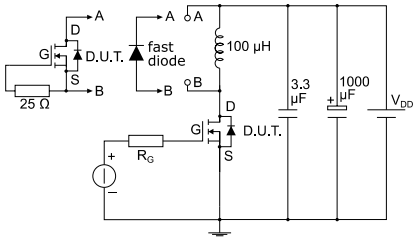


Figure 17: Unclamped inductive load test circuit

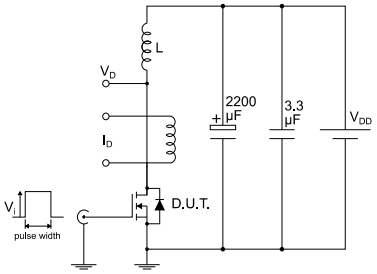


Figure 18: Unclamped inductive waveform

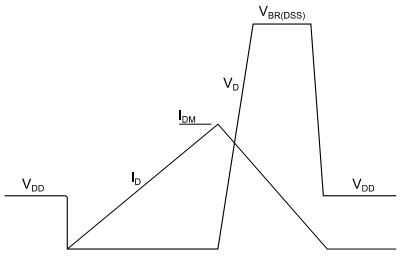
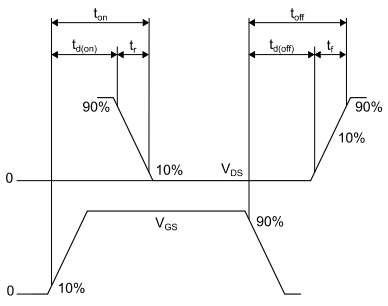


Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 20: D²PAK (TO-263) type A package outline

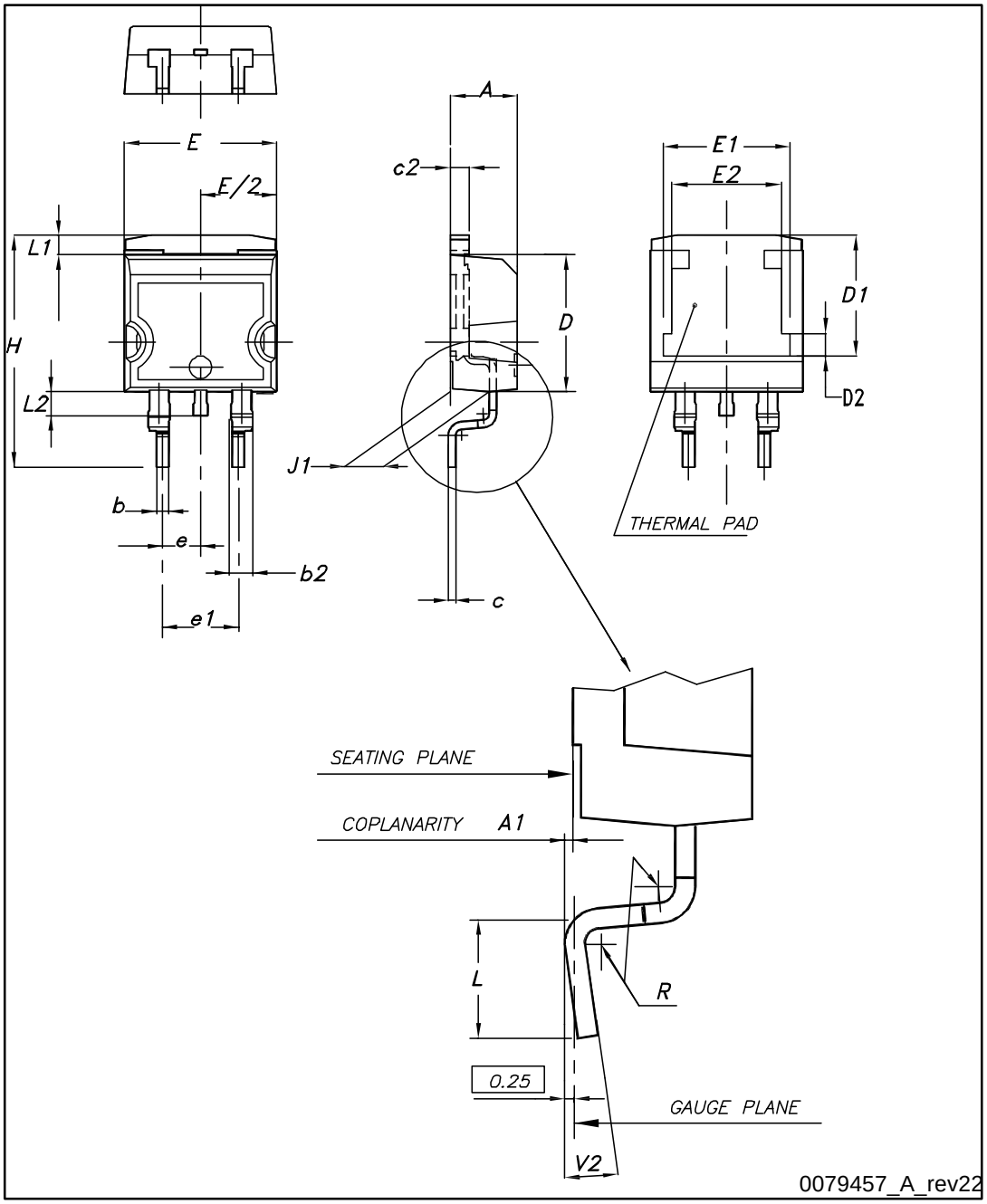
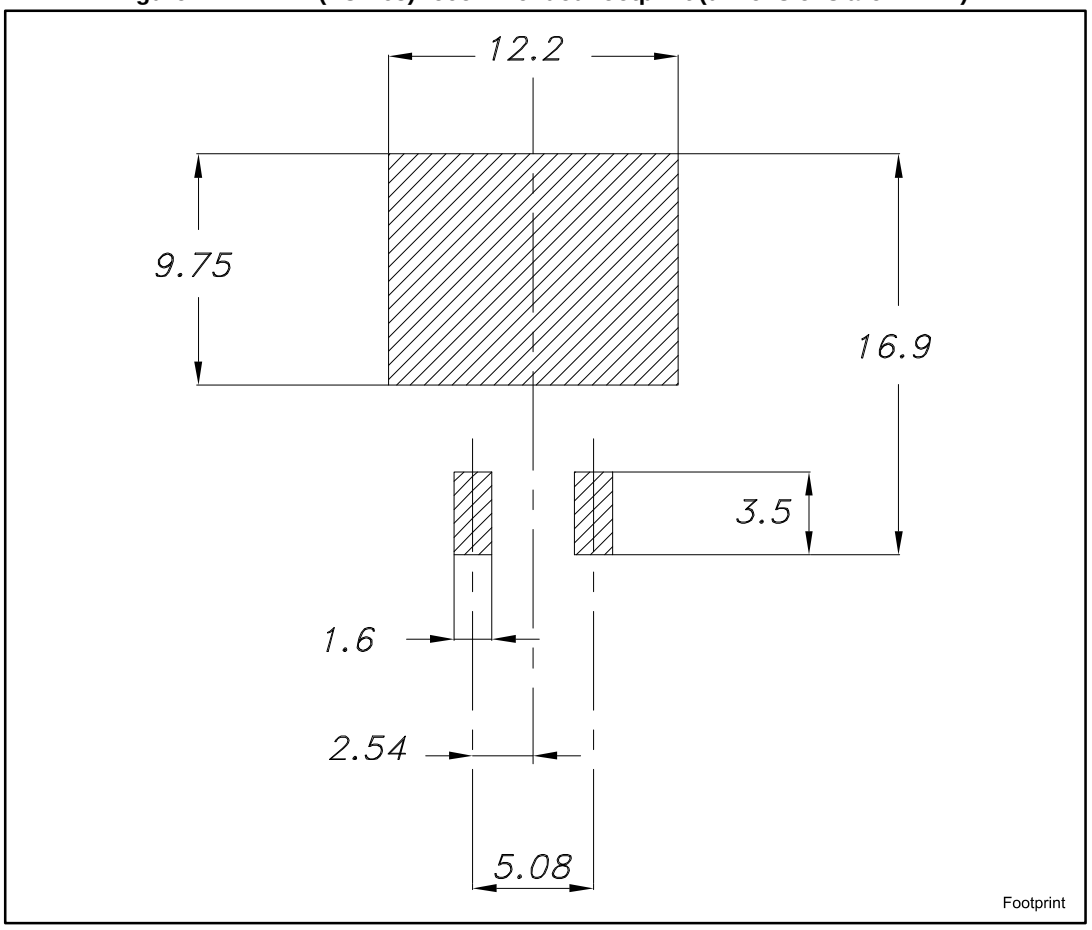


Table 10: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 21: D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 D²PAK packing information

Figure 22: Tape

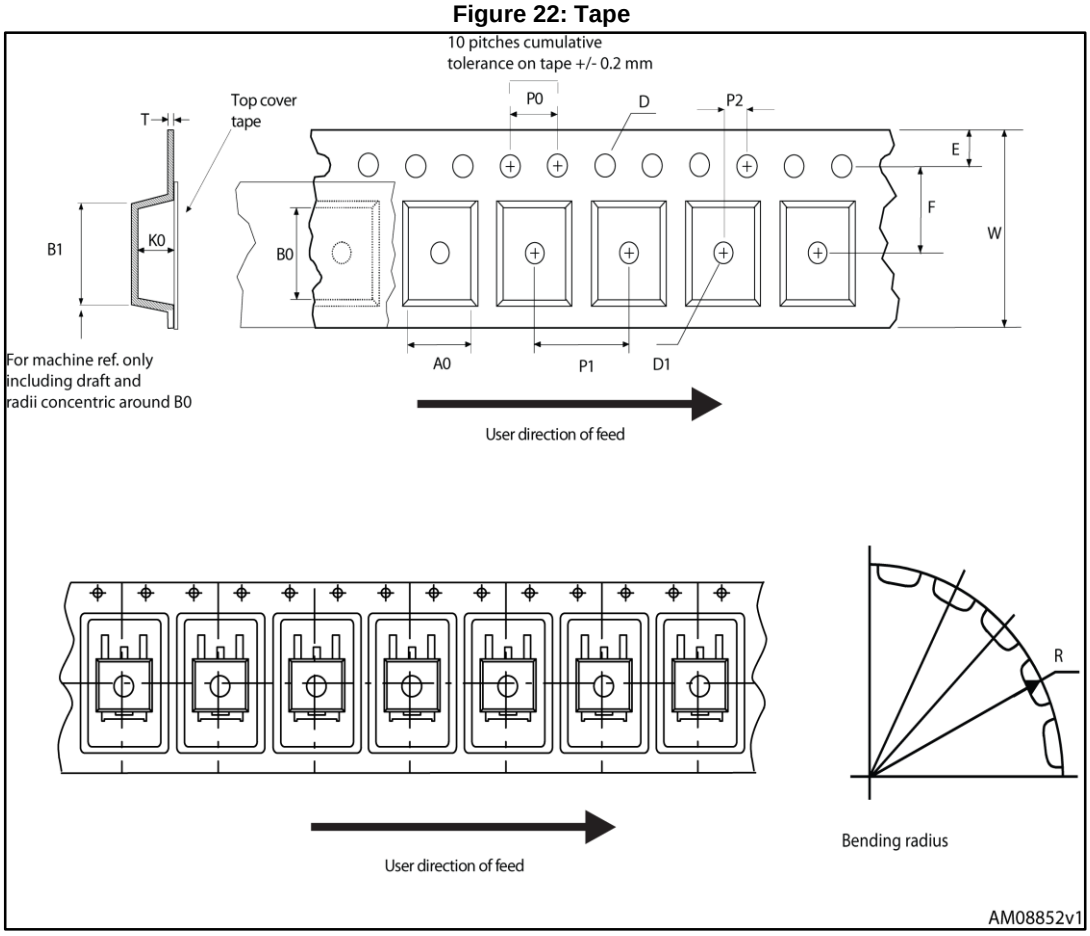


Figure 23: Reel

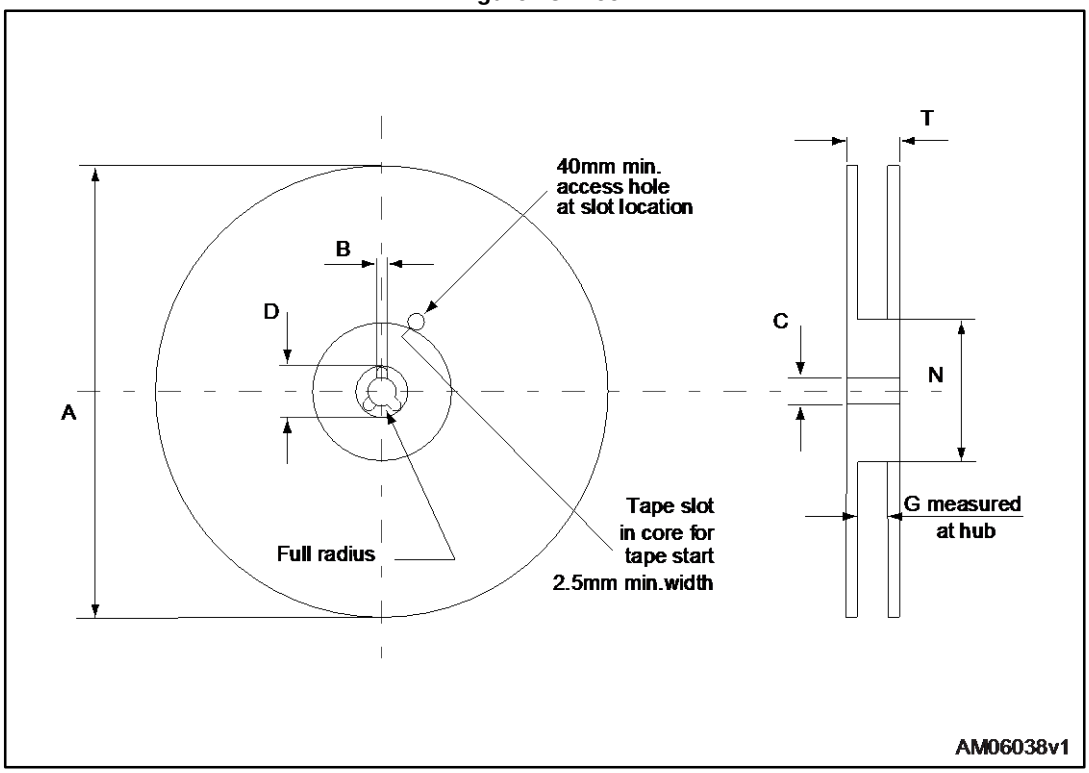


Table 11: D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 12: Document revision history

Date	Revision	Changes
19-Aug-2015	1	Initial version

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